## NB3M8304C

## 3．3 V 200 MHz $1: 4$ LVCMOS／LVTTL Low Skew Fanout Buffer

## Description

The NB3M8304C is 1：4 fanout buffer with LVCMOS／LVTTL input and output．The device supports the core supply voltage of $3.3 \mathrm{~V}\left(\mathrm{~V}_{\mathrm{DD}}\right.$ pin）and output supply voltage of 2.5 V or $3.3 \mathrm{~V}\left(\mathrm{~V}_{\text {DDO }} \mathrm{pin}\right)$ ．The $\mathrm{V}_{\mathrm{DDO}}$ pin powers the four single ended LVCMOS／LVTTL outputs．

The NB3M8304C is Form，Fit and Function（pin to pin）compatible to ICS8304 and ICS8304I．The NB3M8304C is qualified for industrial operating temperature range．

## Features

－Input Clock Frequency up to 200 MHz
－Low Output to Output Skew： 45 ps max
－Low Part to Part Skew： 500 ps max
－Low Additive RMS Phase Jitter
－Input Clock Accepts LVCMOS／LVTTL Levels
－Operating Voltage：
－Core Supply：VDD $=3.3 \mathrm{~V} \pm 5 \%$
－Output Supply： $\mathrm{V}_{\mathrm{DDO}}=3.3 \mathrm{~V} \pm 5 \%$ or $2.5 \mathrm{~V} \pm 5 \%$
－Operating Temperature Range：
－Industrial：$-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$
－These Devices are $\mathrm{Pb}-$ Free and are RoHS Compliant

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A＝Assembly Location
L＝Wafer Lot
Y＝Year
W＝Work Week
－＝Pb－Free Package
（Note：Microdot may be in either location）

## ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet．




Figure 1．Block Diagram

## NB3M8304C



Figure 2. Pin Configuration (Top View)

Table 1. PIN DESCRIPTION

| Pin Number | Name | Type | Description |
| :---: | :---: | :---: | :--- |
| 1 | VDDO | Output Power | Clock output Supply pin. |
| 2 | VDD | Input and Core Power | Input and Core Supply pin. |
| 3 | CLK | LVCMOS/LVTTL Input | Clock Input. Internally pull-down. |
| 4 | GND | Ground | Supply Ground. |
| $5,6,7,8$ | Q[0:3] | LVCMOS/LVTTL Output | LVCMOS/LVTTL Clock output. |

Table 2. MAXIMUM RATINGS

| Symbol | Parameter | Condition | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{DD}}, \mathrm{V}_{\text {DDO }}$ | Power Supply |  | - | 4.6 | V |
| $V_{1}$ | Input Voltage |  | -0.5 | $V_{D D}+0.5$ | V |
| $\mathrm{T}_{\text {stg }}$ | Storage Temperature |  | -65 | +150 | ${ }^{\circ} \mathrm{C}$ |
| $\theta_{J A}$ | Thermal Resistance (Junction-to-Ambient) SOIC-8 | $\begin{gathered} 0 \text { lfpm } \\ 500 \text { lfpm } \end{gathered}$ |  | $\begin{aligned} & 80 \\ & 55 \end{aligned}$ | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\theta_{J c}$ | Thermal Resistance (Junction to Case) (Note 1) |  |  | 12-17 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\mathrm{T}_{\text {sol }}$ | Wave Solder | 3 sec |  | 265 | ${ }^{\circ} \mathrm{C}$ |
| MSL | Moisture Sensitivity SOIC-8 | Indefinite Time Out of Drypack (Note 2) | Level 1 |  |  |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. JEDEC standard multilayer board - 2S2P (2 signal, 2 power)
2. For additional information, see Application Note AND8003/D.

Table 3. DC OPERATING CHARACTERISTICS ( $\mathrm{V}_{\mathrm{DD}}=3.3 \mathrm{~V} \pm 5 \% ; \mathrm{T}_{\mathrm{A}}=-40^{\circ} \mathrm{C}$ to $\left.+85^{\circ} \mathrm{C}\right)$

| Symbol | Parameter | Condition | Min | Typ | Max | Unit |
| :---: | :--- | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{R}_{\mathrm{IN}}$ | Input Pull-down Resistor (CLK Pin) |  |  | 51 |  | $\mathrm{k} \Omega$ |
| $\mathrm{C}_{\mathrm{IN}}$ | Input Capacitance |  |  | 4 |  | pF |
| $\mathrm{R}_{\mathrm{OUT}}$ | Output Impedance (Note 3) |  | 5 | 7 | 12 | $\Omega$ |
| $\mathrm{C}_{\mathrm{PD}}$ | Power Dissipation Capacitance (per output) | $\mathrm{V}_{\mathrm{DD}}=\mathrm{V}_{\mathrm{DDO}}=3.465 \mathrm{~V}$ |  | 15 |  | pF |
| $\mathrm{V}_{\mathrm{DD}}$ | Core Supply Voltage |  | 3.135 | 3.3 | 3.465 | V |
| $\mathrm{I}_{\mathrm{IH}}$ | Input High Current | $\mathrm{V}_{\mathbb{I N}}=\mathrm{V}_{\mathrm{DD}}=3.465 \mathrm{~V}$ |  |  | 150 | $\mu \mathrm{~A}$ |
| $\mathrm{I}_{\mathrm{IL}}$ | Input Low Current | $\mathrm{V}_{\mathrm{DD}} 3.465 \mathrm{~V}, \mathrm{~V}_{\mathrm{IN}}=0.0 \mathrm{~V}$ | -0.5 |  |  | $\mu \mathrm{~A}$ |

3. Outputs terminated with $50 \Omega$ to $V_{\text {DDO }} / 2$. See Figure 4 for supply considerations.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Table 4. DC OPERATING CHARACTERISTICS $\left(T_{A}=-40^{\circ} \mathrm{C}\right.$ to $\left.+85^{\circ} \mathrm{C}\right)$

| Symbol | Parameter | Condition | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{DD}}=3.3 \mathrm{~V} \pm 5 \%, \mathrm{~V}_{\text {DDO }}=2.5 \mathrm{~V} \pm 5 \%$ |  |  |  |  |  |
| $\mathrm{V}_{\text {DDO }}$ | Output Supply Voltage |  | 2.375 | 2.625 | V |
| $\mathrm{V}_{\mathrm{OH}}$ | Output HIGH Voltage | $\mathrm{IOH}=-100 \mu \mathrm{~A}$ | 2.2 |  | V |
|  |  | $\mathrm{IOH}=-16 \mathrm{~mA}$ | 2.1 |  |  |
|  |  | $50 \Omega$ to $\mathrm{V}_{\mathrm{DDO}} / 2$ | 2.1 |  |  |
| $\mathrm{V}_{\text {OL }}$ | Output LOW Voltage | $\mathrm{IOL}=16 \mathrm{~mA}$ |  | 0.25 |  |
|  |  | $\mathrm{loL}=100 \mu \mathrm{~A}$ |  | 0.2 | V |
|  |  | $50 \Omega$ to $\mathrm{V}_{\mathrm{DDO}} / 2$ |  | 0.5 |  |
| $\mathrm{V}_{\mathrm{DD}}=\mathrm{V}_{\mathrm{DDO}}=3.3 \mathrm{~V} \pm 5 \%$ |  |  |  |  |  |
| $\mathrm{V}_{\text {DDO }}$ | Output Supply Voltage |  | 3.135 | 3.465 | V |
| $\mathrm{V}_{\mathrm{OH}}$ | Output HIGH Voltage | $\mathrm{IOH}=-16 \mathrm{~mA}$ | 2.9 |  | V |
|  |  | $\mathrm{I}_{\mathrm{OH}}=-100 \mu \mathrm{~A}$ | 3 |  |  |
|  |  | $50 \Omega$ to $\mathrm{V}_{\mathrm{DDO}} / 2$ | 2.6 |  |  |
| $\mathrm{V}_{\text {OL }}$ | Output LOW Voltage | $\mathrm{I}_{\mathrm{OL}}=16 \mathrm{~mA}$ |  | 0.25 |  |
|  |  | l OL $=100 \mu \mathrm{~A}$ |  | 0.15 | V |
|  |  | $50 \Omega$ to $\mathrm{V}_{\mathrm{DDO}} / 2$ |  | 0.5 |  |

Table 5. DC OPERATING CHARACTERISTICS
( $\mathrm{T}_{\mathrm{A}}=-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C} ; \mathrm{V}_{\mathrm{DD}}=\mathrm{V}_{\mathrm{DDO}}=3.3 \mathrm{~V} \pm 5 \% ; \mathrm{V}_{\mathrm{DD}}=3.3 \mathrm{~V} \pm 5 \%, \mathrm{~V}_{\mathrm{DDO}}=2.5 \mathrm{~V} \pm 5 \%$ )

| Symbol | Parameter | Condition | Min | Max | Unit |
| :---: | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{I}_{\mathrm{DD}}$ | Quiescent Power Supply Current | No Load |  | 15 | mA |
| $\mathrm{I}_{\mathrm{DDO}}$ | Quiescent Power Supply Current | No Load |  | 8 | mA |
| $\mathrm{~V}_{\mathrm{IH}}$ | Input HIGH Voltage |  | 2 | $\mathrm{~V}_{\mathrm{DD}}+0.3$ | V |
| $\mathrm{~V}_{\mathrm{IL}}$ | Input LOW Voltage |  | -0.3 | 1.3 | V |

Table 6. AC CHARACTERISTICS (Note 4)

| Symbol | Parameter | Condition | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{T}_{\mathrm{A}}=-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C} ; \mathrm{V}_{\mathrm{DD}}=3.3 \mathrm{~V} \pm 5 \%, \mathrm{~V}_{\text {DDO }}=3.3 \mathrm{~V} \pm 5 \%$ |  |  |  |  |  |  |
| $\mathrm{F}_{\text {IN }}$ | Input Frequency |  |  |  | 200 | MHz |
| tpLH | Propagation Delay (Note 5) | Fin $=200 \mathrm{MHz}$ | 1.9 |  | 3.3 | ns |
| tSKEW | Output to Output Skew(Note 6) |  |  | 25 | 45 | ps |
|  | Part to Part Skew (Note 6) |  |  | 250 | 800 | ps |
| tskewdi | Output Duty Cycle (see Figure 3) | Fin $=200 \mathrm{MHz}$ | 40 |  | 60 | \% |
| tr/tf | Output rise and fall times (Note 7) | $\begin{gathered} 30 \% \text { to } 70 \%, \mathrm{RS}=33 \Omega, \\ \mathrm{CL}=10 \mathrm{pF} \end{gathered}$ | 250 |  | 500 | ps |

$\mathrm{T}_{\mathrm{A}}=-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C} ; \mathrm{V}_{\mathrm{DD}}=3.3 \mathrm{~V} \pm 5 \%, \mathrm{~V}_{\mathrm{DDO}}=2.5 \mathrm{~V} \pm 5 \%$

| $\mathrm{F}_{\text {IN }}$ | Input Frequency |  |  |  | 200 | MHz |
| :---: | :--- | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{t}_{\text {PLH }}$ | Propagation Delay (Note 5) | Fin $=200 \mathrm{MHz}$ | 2.2 |  | 3.7 | ns |
| t SKEW | Output to Output Skew(Note 6) |  |  | 25 | 45 | ps |
|  | Part to Part Skew (Note 6) |  |  | 250 | 500 | ps |
| tsKEWDC | Output Duty Cycle (see Figure 3) | Fin $=200 \mathrm{MHz}$ | 40 |  | 60 | $\%$ |
| tr/tf | Output rise and fall times (Note 7) | $30 \%$ to $70 \%, \mathrm{RS}=33 \Omega$, <br> $\mathrm{CL}=10 \mathrm{pF}$ | 200 |  | 500 | ps |

4. Clock input with $50 \%$ duty cycle. Outputs terminated with $50 \Omega$ to $\mathrm{V}_{\mathrm{DDO}} / 2$. See Figures 3 and 4 .
5. Measured from $\mathrm{V}_{\mathrm{DD}} / 2$ of the input to $\mathrm{V}_{\mathrm{DDO}} / 2$ of the output.
6. Similar input conditions and the same supply voltages. Measured at $V_{D D O} / 2$. See Figures 3 and 4 .
7. RS is Series Resistance and CL is Load Capacitance at the clock outputs.

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.


Figure 3. AC Reference Measurement


| Spec Condition: | TEST SETUP $\mathrm{V}_{\mathrm{DD}}:$ | TEST SETUP $\mathrm{V}_{\text {DDO }}:$ | TEST SETUP DUT GND: |
| :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{DD}}=\mathrm{V}_{\mathrm{DDO}}=3.3 \mathrm{~V} \pm 5 \%$ | $1.65 \mathrm{~V} \pm 5 \%$ | $1.65 \mathrm{~V} \pm 5 \%$ | $-1.65 \mathrm{~V} \pm 5 \%$ |
| $\mathrm{~V}_{\mathrm{DD}}=3.3 \mathrm{~V} \pm 5 \% ;$ | $2.05 \mathrm{~V} \pm 5 \%$ | $1.25 \mathrm{~V} \pm 5 \%$ | $-1.25 \mathrm{~V} \pm 5 \%$ |
| $\mathrm{~V}_{\mathrm{DDO}}=2.5 \mathrm{~V} \pm 5 \%$ |  |  |  |

Figure 4. Output Driver Typical Device Evaluation and Termination Setup
ORDERING INFORMATION

| Device | Package | Shipping $^{\dagger}$ |
| :--- | :---: | :---: |
| NB3M8304CDG | SOIC-8 <br> (Pb-Free) | 98 Units / Rail |
| NB3M8304CDR2G | SOIC-8 <br> (Pb-Free) | $2500 /$ Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.


SOIC-8 NB
CASE 751-07
ISSUE AK
SCALE 1:1
DATE 16 FEB 2011


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW
7. 751-01 THRU 751-06 AR
STANDARD IS 751-07.

| DIM | MILLIMETERS |  | INCHES |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
|  | 4.80 | 5.00 | 0.189 | 0.197 |
| B | 3.80 | 4.00 | 0.150 | 0.157 |
| C | 1.35 | 1.75 | 0.053 | 0.069 |
| D | 0.33 | 0.51 | 0.013 | 0.020 |
| G | 1.27 BSC |  | 0.050 BSC |  |
| H | 0.10 | 0.25 | 0.004 | 0.010 |
| J | 0.19 | 0.25 | 0.007 | 0.010 |
| K | 0.40 | 1.27 | 0.016 | 0.050 |
| M | 0 | $0^{\circ}$ | $8^{\circ}$ | 0 |
|  | $\circ$ | 8 |  |  |
| N | 0.25 | 0.50 | 0.010 | 0.020 |
| S | 5.80 | 6.20 | 0.228 | 0.244 |

## GENERIC

MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
= Year
$\begin{array}{ll}\mathrm{W} & =\text { Work Week } \\ \text { - } & =\text { Pb-Free Package }\end{array}$
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot " $\mathrm{=}$ ", may or may not be present. Some products may not follow the Generic Marking.
*For additional information on our $\mathrm{Pb}-$ Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## STYLES ON PAGE 2

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CASE 751-07
ISSUE AK
DATE 16 FEB 2011

STYLE

| PIN 1. | EMITTER |
| ---: | :--- |
| 2. | COLLECTOR |
| 3. | COLLECTOR |
| 4. | EMITTER |
| 5. | EMITTER |
| 6. | BASE |
| 7. | BASE |
| 8. | EMITTER |
| STYLE 5: |  |
| PIN 1. | DRAIN |
| 2. | DRAIN |
| 3. | DRAIN |
| 4. | DRAIN |
| 5. | GATE |
| 6. | GATE |
| 7. | SOURCE |
| 8. | SOURCE |

STYLE 9:
PIN 1. EMITTER, COMMON
COLLECTOR, DIE \#1 COLLECTOR, DIE \#2 EMITTER, COMMON EMITTER, COMMON BASE, DIE \#2
BASE, DIE \#1
8. EMITTER, COMMON

STYLE 13:
PIN 1. N.C.
2. SOURCE
3. SOURCE

GATE
DRAIN
DRAIN
DRAIN
8. DRAIN

STYLE 17:
PIN 1. VCC
V2OUT
V10UT
V10UT
TXE
RXE
VEE
7. GND
8. ACC

STYLE 21:
PIN 1. CATHODE 1
2. CATHODE 2
3. CATHODE 3

CATHODE 4
CATHODE 5
6. COMMON ANODE
7. COMMON ANODE
8. CATHODE 6

STYLE 25:
PIN 1. VIN
2. $\mathrm{N} / \mathrm{C}$

REXT
GND
IOUT
IOUT
IOUT
8. IOUT

## STYLE 29

PIN 1. BASE, DIE \#
EMITTER, \#1
BASE, \#2
. EMITTER, \#2
5. COLLECTOR, \#2
6. COLLECTOR, \#2
7. COLLECTOR, \#1
8. COLLECTOR, \#1

STYLE
PIN 1. COLIECTOR,
2. COLLECTOR, \#
3. COLLECTOR, \#2

COLLECTOR, \#2
BASE, \#2
. EMITTER, \#2
7. BASE, \#1
8. EMITTER, \#1

STYLE 6:
PIN 1. SOURCE
DRAIN
3. DRAIN
4. SOURCE

SOURCE
6. GATE
7. GATE
8. SOURCE

STYLE 10:
PIN 1. GROUND
2. BIAS 1
3. OUTPUT

GROUND
GROUND
BIAS 2
7. INPUT
8. GROUND

STYLE 14
PIN 1. N-SOURCE
2. N-GATE
. P-SOURCE
P-GATE
5.DRAIN
6. P-DRAIN
7. N-DRAIN
8. N -DRAIN

STYLE 18
PIN 1. ANODE
2. ANODE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. CATHODE
8. CATHODE

STYLE 22 :
PIN 1. I/O LINE
2. COMMON CATHODE/VCC
3. COMMON CATHODE/VCC
4. I/O LINE 3
5. COMMON ANODE/GND
6. I/O LINE 4
7. I/O LINE 5
8. COMMON ANODE/GND

STYLE 26:
PIN 1. GND
2. $\mathrm{dv} / \mathrm{dt}$
3. ENABLE
4. ILIMIT

SOURCE
SOURCE
SOURCE
8. VCC

STYLE 30:
PIN 1. DRAIN 1
2. DRAIN 1
. GATE 2
4. SOURCE 2
5. SOURCE 1/DRAIN 2
. SOURCE 1/DRAIN 2
SOURCE 1/DRAIN 2
8. GATE 1

STYLE 3
STYLE
2. DRAIN, DIE
2. DRAIN, \#1
2. DRAIN, \#
3. DRAIN, \#2
4. DRAIN, \#2
5. GATE, \#2
7. GATE, \#1
8. SOURCE, \#1

## STYLE 7

PIN 1. INPUT
2. EXTERNAL BYPASS
3. THIRD STAGE SOURCE
4. GROUND
5. DRAIN
6. GATE 3
7. SECOND STAGE Vd
8. FIRST STAGE Vd

## STYLE 11:

PIN 1. SOURCE
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

## STYLE 15:

PIN 1. ANODE 1
2. ANODE 1
3. ANODE 1
4. ANODE 1
5. CATHODE, COMMON
6. CATHODE, COMMON
7. CATHODE, COMMON
8. CATHODE, COMMON

## STYLE 19:

PIN 1. SOURCE
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN
6. MIRROR 2
7. DRAIN 1
8. MIRROR 1

## STYLE 23:

PIN 1. LINE 1 IN
2. COMMON ANODE/GND
3. COMMON ANODE/GND
4. LINE 2 IN
5. LINE 2 OUT
6. COMMON ANODE/GND
7. COMMON ANODE/GND
8. LINE 1 OUT

STYLE 27:
PIN 1. ILIMIT
2. OVLO
3. UVLO
4. INPUT+
5. INPUT+
5. SOURCE
6. SOURCE
7. SOURCE
8. DRAIN

STYLE 4:
PIN 1. ANODE
2. ANODE
3. ANODE
4. ANODE
5. ANODE
6. ANODE
8. COMMON CATHODE

## STYLE 8:

PIN 1. COLLECTOR, DIE \#1
2. BASE, \#1
3. BASE, \#2
4. COLLECTOR, \#2
5. COLLECTOR, \#2
6. EMITTER, \#2
7. EMITTER, \#1
8. COLLECTOR, \#1

## STYLE 12

PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

## STYLE 16:

PIN 1. EMITTER, DIE \#1
2. BASE, DIE \#1
3. EMITTER, DIE \#2
3. EMITTER, DIE
4. BASE, DIE \#2
4. BASE, DIE \#2
6. COLLECTOR, DIE \#2
7. COLLECTOR, DIE \#1
8. COLLECTOR, DIE \#1

## STYLE 20:

PIN 1. SOURCE (N)
2. GATE (N)
3. SOURCE (P)
4. GATE (P)
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 24
PIN 1. BASE
2. EMITTER
3. COLLECTOR/ANODE
4. COLLECTOR/ANODE
5. CATHODE
6. CATHODE
7. COLLECTOR/ANODE
8. COLLECTOR/ANODE

## STYLE 28:

PIN 1. SW_TO_GND
2. DASIC $\bar{O} F F$
3. DASIC_SW_DET
4. GND
5. V_MON
6. VBULK
7. VBULK
8. VIN

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